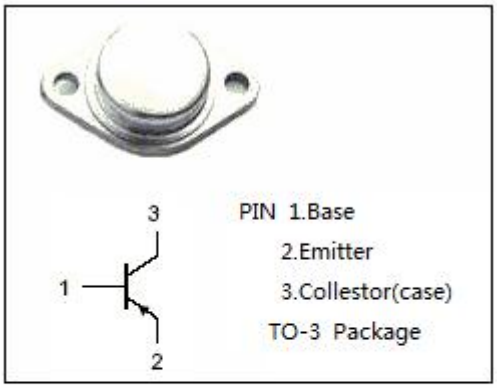
isc Silicon PNP Power Transistor 2SB506

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$= -100V(Min)
- Low Collector Saturation Voltage-
  : $V_{CE(sat)}$= -1.0V(Max.) @I_C= -5A
- Wide area of safe operation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

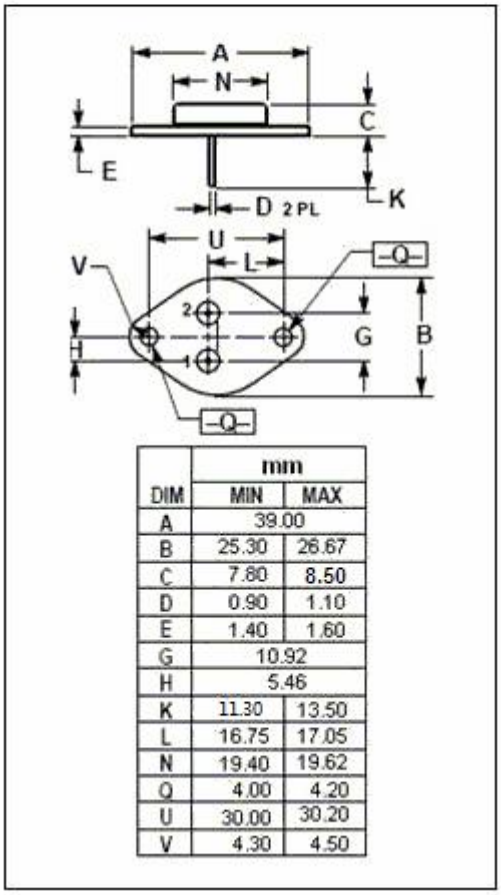


APPLICATIONS

- Designed for low frequency power amplifier and switching applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-150	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current-Continuous	-5	A
P_C	Collector Power Dissipation @Tc=25℃	60	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

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ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= -10mA; I_B= 0	-100			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= -1mA; I_C= 0	-7			V
$V_{(BR)CBO}$	Collector-Base breakdown voltage	I_C=-1mA; I_E= 0	-150			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -5A; I_B= -0.5A			-1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -5A; I_B= -0.5A			-1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -150V; I_E= 0			-10	μA
I_{CEO}	Collector Cutoff Current	V_{CE}= -100V; I_B= 0			-100	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -7V; I_C= 0			-10	μA
h_{FE}	DC Current Gain	I_C= -1A; V_{CE}= -5V	35		200	
f_T	Current-Gain—Bandwidth Product	I_C=-0.3A ; V_{CE}= -10V		20		MHz